Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- · Trench MOSFET technology
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Tin-plated 100 % solderable side pads for optical solder inspection
- ElectroStatic Discharge (ESD) protection > 2 kV
- · AEC-Q101 qualified

3. Applications

- Relay driver
- · High-speed line driver
- · Low-side load switch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	60	V	
V_{GS}	gate-source voltage			-20	-	20	V	
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	4	Α	
Static characte	Static characteristics							
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 4 \text{ A}; T_j = 25 ^{\circ}\text{C}$		-	42	56	mΩ	

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	15/	D
2	D	drain	7 7	
3	G	gate	2 5	G $+$ $+$ $+$
4	S	source	3 8 4	
5	D	drain	Transparent top view	
6	D	drain	DFN2020MD-6 (SOT1220)	8
7	D	drain		017aaa255
8	S	source		

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMPB55ENEA	DFN2020MD-6	DFN2020MD-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220			

7. Marking

Table 4. Marking codes

Type number	Marking code
PMPB55ENEA	2G

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

urce voltage rce voltage rent	T _j = 25 °C V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-20	60 20	V
	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-20	20	V
rent	V _{GS} = 10 V; T _{amb} = 25 °C	[1]			
		-	-	4	Α
	V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	2.5	Α
in current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	16	Α
	$T_{j(init)}$ = 25 °C; I_D = 1.3 A; DUT in avalanche (unclamped)		-	12.6	mJ
total power dissipation	T _{amb} = 25 °C	[1]	-	1.65	W
	T _{sp} = 25 °C		-	15.6	W
temperature			-55	150	°C
temperature			-55	150	°C
temperature			-65	150	°C
			,		
urrent	T _{amb} = 25 °C	[1]	-	1.2	Α
		•			
atic discharge	НВМ	[2]	-	2000	V
	ain current etitive drain- evalanche ver dissipation temperature temperature temperature temperature	tain current $T_{amb} = 25 ^{\circ}\text{C}$; single pulse; $t_p \le 10 \mu \text{s}$ settitive drainavalanche $T_{j(init)} = 25 ^{\circ}\text{C}$; $I_D = 1.3 \text{A}$; DUT in avalanche (unclamped) $T_{amb} = 25 ^{\circ}\text{C}$ $T_{sp} = 25 ^{\circ}\text{C}$ temperature temperature $T_{amb} = 25 ^{\circ}\text{C}$ temperature $T_{amb} = 25 ^{\circ}\text{C}$ temperature $T_{amb} = 25 ^{\circ}\text{C}$	tain current $T_{amb} = 25 ^{\circ}\text{C}$; single pulse; $t_p \le 10 \mu \text{s}$ settitive drainavalanche $T_{j(init)} = 25 ^{\circ}\text{C}$; $I_D = 1.3 \text{A}$; DUT in avalanche avalanche (unclamped) $T_{amb} = 25 ^{\circ}\text{C}$ [1] $T_{sp} = 25 ^{\circ}\text{C}$ temperature temperature $T_{amb} = 25 ^{\circ}\text{C}$ [1] temperature $T_{amb} = 25 ^{\circ}\text{C}$ [1] temperature	tain current $T_{amb} = 25 ^{\circ}\text{C}$; single pulse; $t_p \le 10 \mu s$ - etitive drainavalanche $T_{j(init)} = 25 ^{\circ}\text{C}$; $I_D = 1.3 \text{A}$; DUT in avalanche $I_{avalanche} = 25 ^{\circ}\text{C}$ avalanche $I_{avalanche} = 25 ^{\circ}\text{C}$ [1] - $I_{avalanche} = 25 ^{\circ}\text{C}$ - temperature $I_{avalanche} = 25 ^{\circ}\text{C}$ - temperature $I_{avalanche} = 25 ^{\circ}\text{C}$ - I_{avala	tain current $T_{amb} = 25 ^{\circ}\text{C}$; single pulse; $t_p \le 10 \mu\text{s}$ - 16 Total partition avalanche $T_{j(init)} = 25 ^{\circ}\text{C}$; $I_D = 1.3 \text{A}$; DUT in avalanche $I_{j(init)} = 25 ^{\circ}\text{C}$ avalanche $I_{j(init)} = 25 ^{\circ}\text{C}$ [1] - 1.65 Total partition $I_{j(init)} = 25 ^{\circ}\text{C}$ - 15.6 Total partition $I_{j(init)} = 25 ^{\circ}\text{C}$ - 15.6 Temperature $I_{j(init)} = 25 ^{\circ}\text{C}$ - 15.0 Total partition $I_{j(init)} = 25 ^{\circ}\text{C}$ - 15.0

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².
- [2] Measured between all pins.

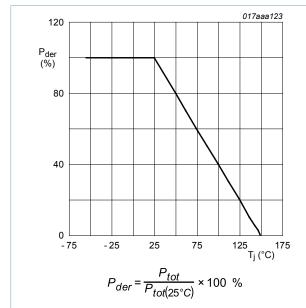


Fig. 1. Normalized total power dissipation as a function of junction temperature

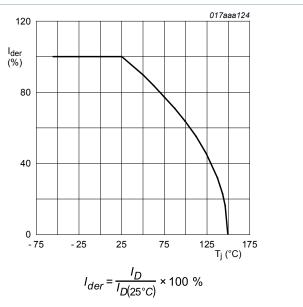


Fig. 2. Normalized continuous drain current as a function of junction temperature

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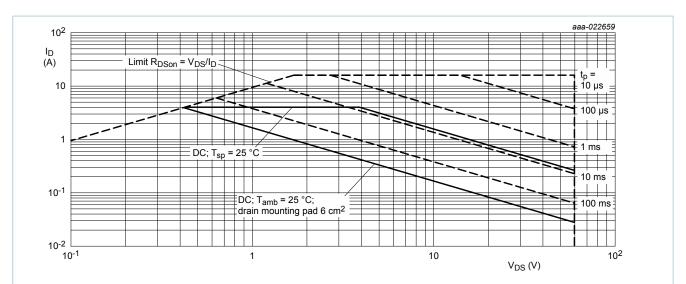


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
uit a)	thermal resistance from junction to ambient		[1]	-	237	273	K/W
			[2]	-	66	76	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	4	8	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².

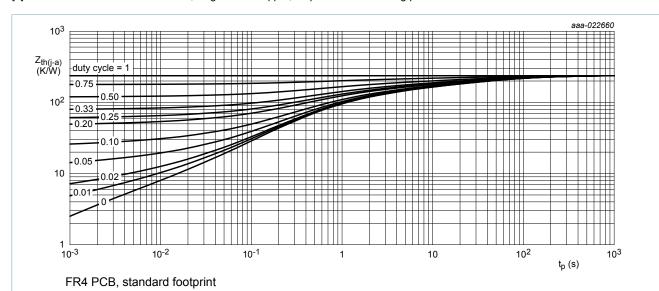


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

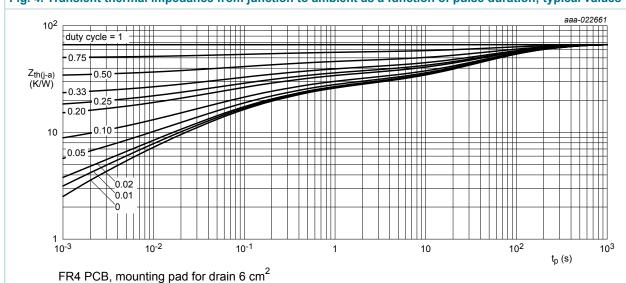


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics				'	_
V _{(BR)DSS}	drain-source breakdown voltage	I_D = 250 μ A; V_{GS} = 0 V; T_j = 25 °C	60	-	-	V
V_{GSth}	gate-source threshold voltage	I _D = 250 μA; V _{DS} =V _{GS} ; T _j = 25 °C	1.3	1.7	2.7	V
I _{DSS}	drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	10	μΑ
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μΑ
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	1	μΑ
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-1	μΑ
Doon	drain-source on-state	V _{GS} = 10 V; I _D = 4 A; T _j = 25 °C	-	42	56	mΩ
	resistance	V _{GS} = 10 V; I _D = 4 A; T _j = 150 °C	-	80	106	mΩ
		V_{GS} = 4.5 V; I_D = 3.5 A; T_j = 25 °C	-	48	69	mΩ
9 _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 4 \text{ A}; T_j = 25 ^{\circ}\text{C}$	-	17	-	S
R _G	gate resistance	f = 1 MHz	-	2.7	-	Ω
Dynamic ch	aracteristics				,	
Q _{G(tot)}	total gate charge	$V_{DS} = 30 \text{ V}; I_D = 4 \text{ A}; V_{GS} = 10 \text{ V};$	-	7.5	12	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	1	-	nC
Q_{GD}	gate-drain charge		-	1.2	-	nC
C _{iss}	input capacitance	V _{DS} = 30 V; f = 1 MHz; V _{GS} = 0 V;	-	435	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	47	-	pF
C _{rss}	reverse transfer capacitance		-	26	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; I_D = 4 \text{ A}; V_{GS} = 10 \text{ V};$	-	4.5	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 ^{\circ}C$	-	4	-	ns
t _{d(off)}	turn-off delay time		-	13.5	-	ns
t _f	fall time		-	7	-	ns
Source-drai	in diode					
V_{SD}	source-drain voltage	I _S = 1.2 A; V _{GS} = 0 V; T _i = 25 °C	-	0.8	1.2	V

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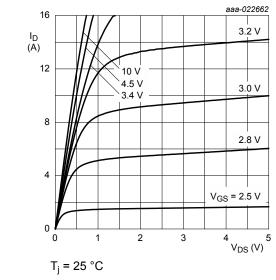


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

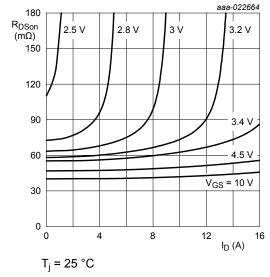


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

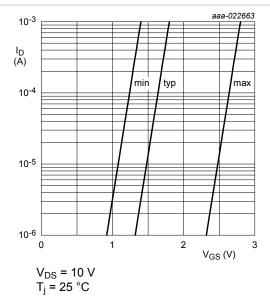


Fig. 7. Sub-threshold drain current as a function of gatesource voltage

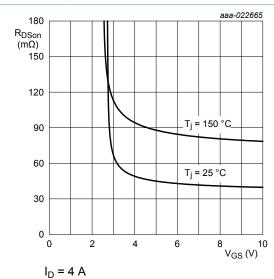


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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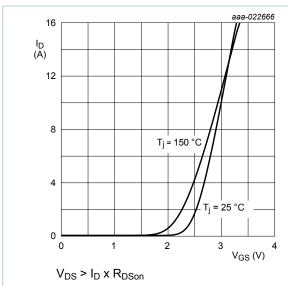


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

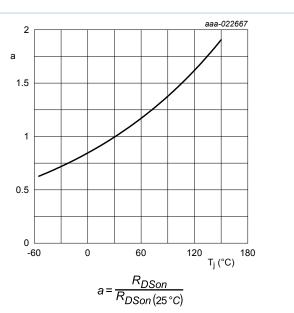


Fig. 11. Normalized drain-source on-state resistance as a function of ambient temperature; typical values

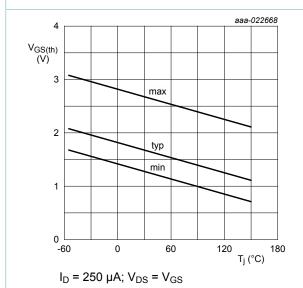


Fig. 12. Gate-source threshold voltage as a function of ambient temperature

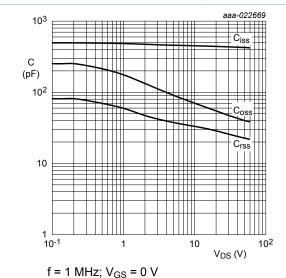


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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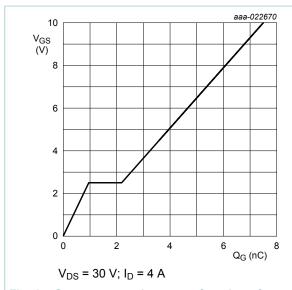


Fig. 14. Gate-source voltage as a function of gate charge; typical values

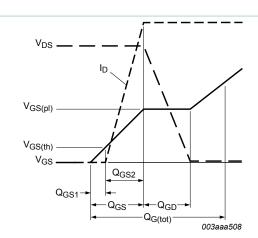


Fig. 15. Gate charge waveform definitions

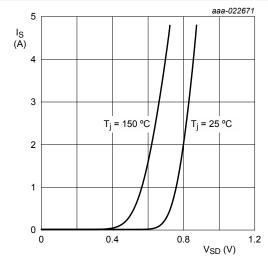
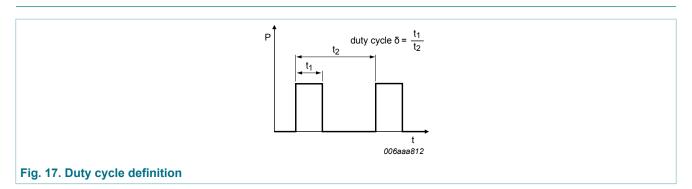


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

 $V_{GS} = 0 V$

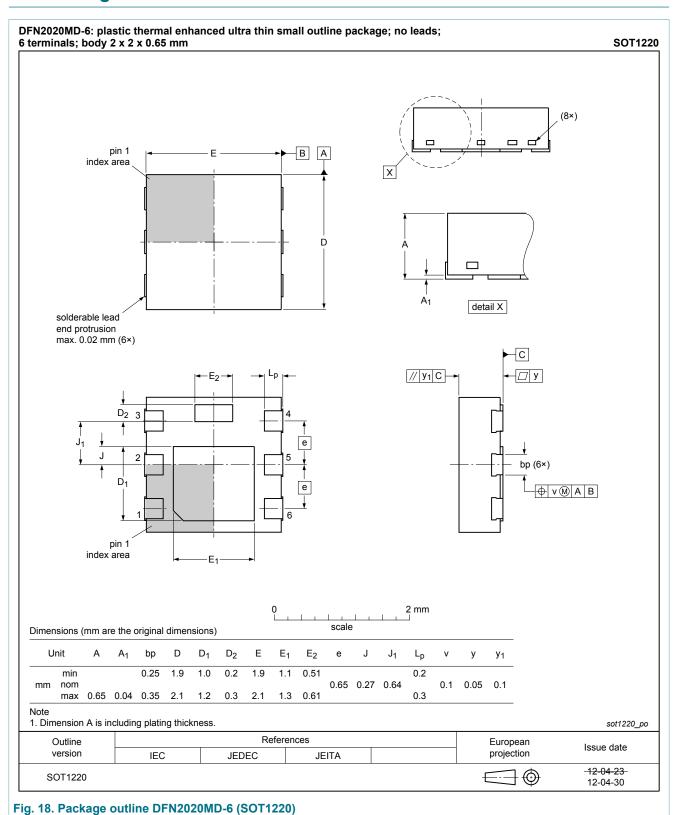


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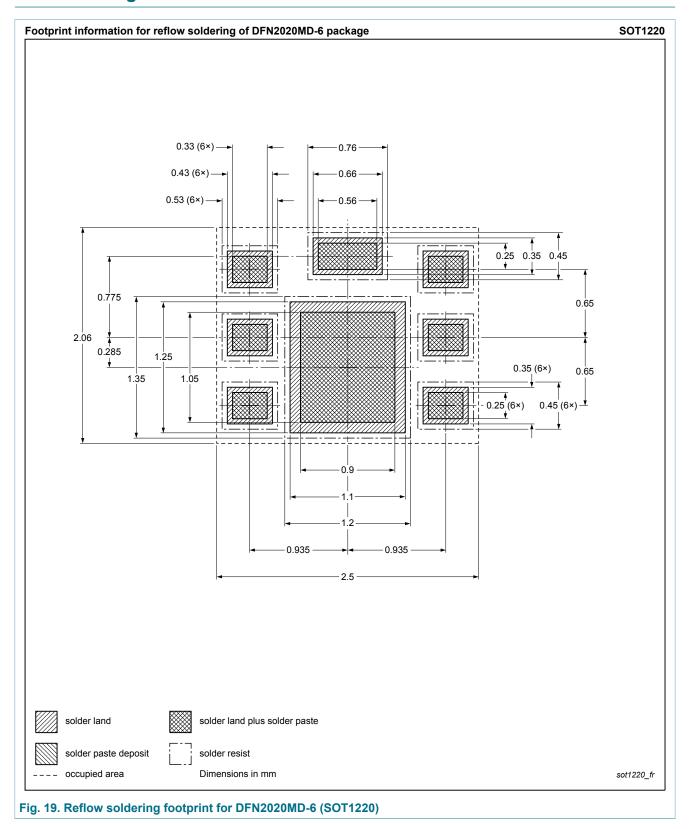
Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline



13. Soldering



14. Revision history

Table 8. Revision history

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Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PMPB55ENEA v.2	20160606	Product data sheet	-	PMPB55ENEA v.1			
Modifications:	Updated Figure 14						
PMPB55ENEA v.1	20160401	Preliminary data sheet	-	-			

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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	Features and benefits

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